Citations for Ion : As

Pub. Year	Authors, Title, Journal Citation and Comments	Citation Numb
1968	Bowman, W. W. Lanzafame, F. M. Cline, C. K. Yu, Yu-Wen Blann, M. **'Recoil Ranges of 0.2 - 5.2 MeV Ions in Vanadium, Nickel, Iron, Zirconium and Gold.'** ***Phys. Rev., 165, 485-93 (1968)*** *Comment : R, dR. Ion(Z1=12-81, E=0.22-5.2 MeV) -> V, Ni, Zr, Au*	**1968-Bowm**
1968	Kleinfelder, W. J. Johnson, W. S. Gibbons, J. F. **'Impurity Distribution Profiles in Ion-Implanted Silicon'** ***Can. J. Phys., 46, 597-606 (1968)*** *Comment : R, dR. 10-70 keV B, N, P, As -> Si (Cryst.)*	**1968-Klei**
1969	Davies, D. E. **'Range of Implanted Boron, Phosphorus, and Arsenic in Silicon'** ***Can. J. Phys., 47, 1750-53 (1969)*** *Comment : R, dR. 0.15-1.8 MeV B, 1.0-1.7 MeV As, 0.5-1.7 MeV P -> Si*	**1969-Davi**
1969	Fairfield, J. M. Crowder, B. L. **'Ion Implantation Doping of Silicon for Shallow Junctions'** ***Trans. Met. Soc. Aime, 245, 469-473 (1969)*** *Comment : R,dR. 70-280 keV B, P, 80-480 keV As -> Si*	**1969-Fair**
1970	Davies, D. E. **'The Implanted Profiles of Boron, Phosphorus, and Arsenic in Silicon from Junction Depth Measurements'** ***Solid-State Elec., 13, 229-237 (1970)*** *Comment : R. 0.1-2.0 MeV B, P, As -> Si*	**1970-Davi**
1971	Crowder, B. L. **'The Influence of the Amorphous Phase on Ion Distributions and Annealing Behavior of Group Iii and Group V Ions Implanted into Silicon'** ***J. Electrochem. Soc., 118, 943-52 (1971)*** *Comment : R,dR. (50-300 keV) B, Al Ga, P, As, Sb, Bi -> Si*	**1971-Crow**
1973	Chu, W. K. Crowder, B. L. Mayer, J. W. Ziegler, J. F. **'Range Distributions of Implanted Ions in SiO2, Si3N4, and Al2O3'** ***Appl. Phys. Letters, 22, 490-92 (1973)*** *Comment : R, dR. Zn, Ga, As, Se, Cd, Te (140-300 keV) -> SiO2, Si3N4, Al2O3*	**1973-Chu**
1973	Chu, W. K. Crowder, B. L. Mayer, J. W. Ziegler, J. F. **'Ranges and Distributions of Ions Implanted into Dielectrics'** ***B.L. Crowder (Ed): Ion Implantation in Semiconductors and Other Materials. Plenum. N. Y. 225-41 (1973)*** *Comment : R.dR. (140-300 keV) Zn, Ga, As, Se, Cd, Te, Zn -> Si, Si3N4, Al2O3*	**1973-Chu 2**
1973	Iwaki, M. Gamo, K. Masuda, K. Namba, S. Ishihara, S. **'Concentration Profiles of Arsenic Implantated in Silicon'** ***B.L. Crowder (Ed): Ion Implantation in Semiconductors and Other Materials. Plenum. N. Y. 111-18 (1973)*** *Comment : R,dR. 35-130 keV As -> Si*	**1973-Iwak**

Citations for Ion : As

Pub. Year	Authors, Title, Journal Citation and Comments	Citation Numb
1973	Schwettmann, F. N. **'Enhanced Diffusion During the Implantation of Arsenic in Silicon'** ***Appl. Phys. Letters, 22, 570-72 (1973)*** *Comment : R, dR. 120 keV As -> Si*	**1973-Schw2**
1973	Tsai, J. C. Morabito, J. M. Lewis, R. K. **'Arsenic Implanted and Implanted Diffused Profiles in Silicon using Secondary Ion Emission and Differential Resistance'** ***B.L. Crowder (Ed): Ion Implantation in Semiconductors and Other Materials. Plenum. N. Y. 87-97 (1973)*** *Comment : R,dR. 40 keV As -> Si*	**1973-Tsai**
1974	Drum, C. M. **'Diffusion of Ion Implanted Antimony and Arsenic in Silicon'** ***J. Electrochem. Soc., 121, 93C (1974)*** *Comment : R, dR. Sb, As (30-80 Kev) -> Si*	**1974-Drum**
1974	Muller, H. Kranz, H. Ryssel, H. Schmid, K. **'Electrical and Backscattering Measurements of Arsenic Implanted Silicon'** ***Appl. Phys., 4, 115-23 (1974)*** *Comment : R. 150-200 keV As -> Si (Cryst.)*	**1974-Mull**
1975	Feuerstein, A. Kalbitzer, S. Oetzmann, H. **'Range Parameters of Heavy Ions at 10 and 35 keV in Silicon'** ***Phys. Letters A, 51, 165-66 (1975)*** *Comment : R, dR. 10-35 keV Ge, As -> Si*	**1975-Feue**
1975	Iwaki, M. Gamo, K. Masuda, K. Namba, S. Ishihara, S. **'Comparison Between Concentration Profiles of Arsenic Implanted in Silicon Measured by Means of Neutron Activation Analysis and Radioactive Ion Implantation'** ***Jap. J. Appl. Phys., 14, 167-68 (1975)*** *Comment : R. 45 keV As -> Si*	**1975-Iwak**
1975	Iwaki, M. Gamo, K. Masuda, K. Namba, S. Ishihara, S. **'Experimental Method for Measuring Both Atom and Carrier Concentration Profiles in the Same Sample of Ion-Implanted Silicon Layers by Radioactive-Ion Implantation'** ***Nucl. Inst. Methods, 127, 93-98 (1975)*** *Comment : R, dR. 45 keV As -> Si*	**1975-Iwak2**
1975	Iwaki, M. Gamo, K. Masuda, K. Namba, S. Ishihara, S. **'Atom and Carrier Profiles in as Implanted Si'** ***Ion Implantation in Semiconductors, Namba (ed.), Plenum, N. Y. 163-68 (1975)*** *Comment : R, dR. 25 keV As -> Si*	**1975-Iwak3**

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Pub. Year	Authors, Title, Journal Citation and Comments	Citation Numb
1975	Ludvik, S. Scharpen, L. Weawer, H. E. **'Measurement of Arsenic Implantation Profiles in Silicon using Electron Spectroscopic Technique'** ***Ion Implantation in Semiconductors, Namba (ed.), Plenum, N. Y. 155-62 (1975)*** *Comment : R, dR. 25, 40 keV 75As -> Si*	**1975-Ludv**
1975	Oetzmann, H. Feuerstein, A. Grahmann, H. Kalbitzer, S. **'Range Parameters of Heavy Ions in Amorphous Targets at LSS-Energies of 0.0006 < Epsilon < 0.3.'** ***Phys. Letters, 55A, 170-172 (1975)*** *Comment : R, dR. 1-60 keV As, Ge, Sb, Au, Bi -> Si, Ge, Al*	**1975-Oetz**
1975	Schimko, R. Richter, C. E. Rogge, K. Schwartz, G. Trapp, M. **'Implanted Arsenic and Boron Concentration Profiles in SiO2 Layers'** ***Phys. Stat. Sol. A, 28, 87-93 (1975)*** *Comment : R,dR. 40-300 keV 11B, 40-150 keV 75As, -> SiO2*	**1975-Schi**
1975	Sigmon, T. W. Chu, W. K. Muller, H. Mayer, J. W. **'Analysis of Arsenic Range Distributions in Silicon'** ***Applied Phys., 5, 347-50 (1975)*** *Comment : R, dR. 50-250 keV As -> Si*	**1975-Sigm**
1976	Grant, W. A. Dodds, D. Williams, J. S. Christodoulides, C. E. Baragiola, R. A. **'Heavy Ion Ranges in Silicon and Aluminum'** ***Ion Implantation in Semiconductors, Ed. by F. Chernow, J. A. Borders, D. K. Brice, 693-703 (1976)*** *Comment : R. 0.01 < Epsilon < 0.8 Cr, Ni, Ga, As, Br, Mo, Cs, La, Nd, Dy, Ta, Pt, Au, Pb -> Si, Al*	**1976-Gran**
1976	Oetzmann, H. Feuerstein, A. Grahmann, H. Kalbitzer, S. **'Range Parameters of Heavy Ions in Silicon and Germanium with Released Energies from 0.01 < epsilon < 10'** ***Meyer, G. Linker and F. Kappeler (Ed.):Ion Beam Surface Layer Analysis, Plenum, N. Y., P. 245-54 (1976)*** *Comment : R, dR. (1-40 keV) Al, Sb, As, Ge, Au, Bi -> Si, Ge*	**1976-Oetz**
1977	Nojima, S. Yamazaki, H. Harada, H. Fujimoto, M. **'Annealing Characteristics of Arsenic-Implanted Silicon'** ***Jap. J. Appl. Phys., 16, 193-194 (1977)*** *Comment : R. 220 keV As -> Si (With Anneal)*	**1977-Noji**
1977	Tsudamoto, K. Akasaka, Y. Horie, K. **'Arsenic Implantation into Polycrystalline Silicon and Diffusion to Silicon Substrate'** ***J. Appl. Phys., 48, 1815-1821 (1977)*** *Comment : R, dR. 60-350 keV As -> Si*	**1977-Tsud**

Citations for Ion : As

Pub. Year	Authors, Title, Journal Citation and Comments	Citation Numb
1977	Tsukamoto, K. Akasaka, Y. Horie, K. **'Range Distribution of Implanted Arsenic in Silicon Dioxide'** ***Jap. J. Appl. Phys., 16, 663-664 (1977)*** *Comment : R, dR. 100-350 keV As -> SiO2*	**1977-Tsuk**
1978	Christodoulides, C. E. Carter, G. Williams, J. S. **'Implant Redistribution in High-Dose Ion Implanted and Annealed Silicon'** ***Intl. Conf. Ion Beam Modification of Materials, Budapest -a (1978)*** *Comment : R, dR. 20-80 keV As, Pb -> Si*	**1978-Chri2**
1978	Furuya, T. Nishi, H. Inada, T. Sakurai, T. **'Channeled-Ion Implantation of Group-III and Group-V Ions into Silicon'** ***J. Appl. Phys., 49, 3918-3921 (1978).*** *Comment : R, dR. 100-300 keV B, P, As, Al, Ga -> Si [111], [110], Random*	**1978-Furu**
1978	Nakamura, K. Kamoshida, M. **'Implanted As Redistribution During Annealing in Oxidizing Ambient'** ***J. Electrochem. Soc., 125, 1518-1521 (1978)*** *Comment : R, dR. 40-120 keV As -> Si*	**1978-Naka**
1978	Nishi, H. Sakurai, T. Furuya, T. **'Electrical Activation of Implanted Arsenic in Silicon During Low Temperature Anneal'** ***J. Electrochem. Soc., 125, 461-466 (1978)*** *Comment : R. 100 keV As -> Si*	**1978-Nish**
1978	North, J. C. Adams, A. C. Richards, G. F. **'Ion Implantation Doping of Polycrystalline Silicon'** ***Extend. Abs. Electrochem., 78, 540 (1978)*** *Comment : R. 150 keV B, As; 300 keV P -> Si*	**1978-Nort**
1978	Ohmura, Y. Inoue, T. Yamamoto, Y. **'Spatially Varied Activation of Ion-Implanted as During the Regrowth of Amorphous Layers in Si'** ***J. Appl. Phys., 49, 3597-3599 (1978)*** *Comment : R. 100 keV As -> Si*	**1978-Ohmu**
1978	Rao, E. V. K. Duhamel, N. Favennec, P. N. L'Haridon, H. **'Investigation of Compensation in Implanted N-GaAs'** ***J. Appl. Phys., 49, 3898-3905 (1978)*** *Comment : R, dR. 200 keV-1 MeV H, B, As -> GaAs*	**1978-Rao**
1978	White, C. W. Christie, W. H. Appleton, B. R. Wilson, S. R. Pronko, P. P. **'Redistribution of Dopants in Ion-Implanted Silicon by Pulsed-Laser Annealing'** ***Appl. Phys. Letters, 33, 662-664 (1978)*** *Comment : R, dR. 35 keV 11B, 80 keV 31P, 100 keV 75As -> Si*	**1978-Whit**

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Pub. Year	Authors, Title, Journal Citation and Comments	Citation Numb
1978	Yokota, K. Tamura, S. Gamo, K. Namba, S. Masuda, K. **'Ion-Implanted Arsenic Profiles in GaAs Encapsulated by SiO2 and Si3N4'** ***Jap. J. Appl. Phys., 17, 1881-1882 (1978)*** *Comment : R, dR. 150 keV As -> Si*	**1978-Yoko**
1979	Hirao, T. Fuse, G. Inoue, K. Takayanagi, S. Yaegashi, Y. **'The Effects of the Recoil-Implanted Oxygen in Si on the Electrical Activation of As afterThrough-Oxide Implantation'** ***J. Appl. Phys., 50, 5251-5256 (1979)*** *Comment : R, dR. 180 keV As -> Si*	**1979-Hira**
1979	Hirao, T. Inoue, K. Takayanagi, S. Yaegashi, Y. **'The Concentration Profiles of Projectiles and Recoiled Nitrogen in Si after Ion Implantation through Si3N4 Films'** ***J. Appl. Phys., 50, 193-201 (1979)*** *Comment : R, dR. 160 keV P -> Si, 355 keV As -> Si, 50 keV B -> Si, 200 keV Ar -> Si*	**1979-Hira2**
1979	Hirao, T. Inoue, K. Yaegashi, Y. Takayanagi, S. **'The Concentration Profiles of Phosphorus, Arsenic and Recoiled Oxygen Atoms in Si by Ion Implantation into SiO2-Si'** ***Jap. J. Appl. Phys., 18, 647-656 (1979)*** *Comment : R, dR. 70-350 keV P, 180 keV As -> Si Through SiO2*	**1979-Hira3**
1979	Kang, S. T. Shimizu, R. Okutani, T. **'Sputtering of Si with keV Ar+ Ions. Ii. Computer Simulation of Sputter Broadening Due to Ion Bombardment in Depth Profiling.'** ***Jap. J. Appl. Phys., 18, 1987-1994 (1979)*** *Comment : R, dR. 45 keV As -> GaAs*	**1979-Kang**
1979	Magee, C. W. **'Depth Profilling of N-Type Dopants in Si and GaAs using Cs+ Bombardment Negative Secondary Ion Mass Spectrometry in Ultrahigh Vacuum'** ***J. Electrochem. Soc., 126, 660-663 (1979)*** *Comment : R, dR. 15 keV H, 80 keV P, 200 keV As -> Si; 200 keV Si, 250 keV S -> GaAs*	**1979-Mage**
1979	Pham, M. T. **'A Very Simple Method for Profiling the Ion-Implanted Si-Surface'** ***Phys. Stat. Sol. A, 49, 261-265 (1979)*** *Comment : R. 30 keV Si, P, B, Ar, As; 12.2 keV In -> Si*	**1979-Pham**
1979	Santry, D. C. Werner, R. D. Westcott, O. M. **'The Range of 120 keV Ions in Solids'** ***IEEE Trans. Nucl. Sci., Ns-26, 1331-1334 (1979)*** *Comment : R, dR. 120 keV Mg, Al, P, S, Cl, K, Ar, Cr, Mn, Cu, Zn, Ga, As, Br, Kr, Rb, Ag, In, Sn, Sb, Te, I, Xe, Cs, Ba, Pr, Au, Hg, Tl, Pb, Bi -> Be, C, Al, Si*	**1979-Sant**

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Pub. Year	Authors, Title, Journal Citation and Comments	Citation Numb
1979	White, C. W. Christie, W. H. Pronko, P. P. Appleton, B. R. Wilson, S. R. **'Dopant Profile Changes Induced by Pulsed Laser Annealing'** ***Rad. Effects, 47, 37-40 (1979)*** *Comment : R, dR. 35-150 keV B, P, As, Sb, Cu, Fe -> Si*	**1979-Whit**
1979	White, C. W. Pronko, P. P. Wilson, S. R. Appleton, B. R. Narayan, J. **'Effects of Pulsed Ruby-Laser Annealing on As and Sb Implanted Silicon'** ***J. Appl. Phys., 50, 3261-3273 (1979)*** *Comment : R, dR. 100 keV 75As, 121Sb -> Si*	**1979-Whit2**
1980	Campisano, S. U. Baeri, P. Foti, G. Ciavola, G. Rimini, E. **'Impurity Redistribution During Laser Irradiation in Ion Implanted Silicon'** ***Rad. Effects, 48, 187-190 (1980)*** *Comment : R, dR. 400 keV As -> Si*	**1980-Camp2**
1980	Hirao, T. Fuse, G. Inoue, K. Takayanagi, S. Yaegashi, Y. **'Electrical Properties of Si Implanted with As through SiO2 Films'** ***J. Appl. Phys., 51, 262-268 (1980)*** *Comment : R, dR. 180 keV As -> Si*	**1980-Hira**
1980	Hirao, T. Inoue, K. Fuse, G. Takayanagi, S. T. Yaegashi, Y. **'The Concentration Profiles of the Recoil Implanted Oxygen in Si afterIon Implantations into SiO2-Si Substrates'** ***Rad. Effects, 47, 95-98 (1980)*** *Comment : R, dR. 100-220 keV P, Ar, As -> Si*	**1980-Hira2**
1980	Kalbitzer, S. Oetzmann, H. **'Ranges and Range Theories'** ***Rad. Effects, 47, 57-72, (1980)*** *Comment : R, dR. .1-2 MeV Bi, Sb, As, Ge, P, Au, Cs, Eu, Gd Tb -> Si, Ge, C, Al*	**1980-Kalb**
1980	Rimini, E. Chu, W. K. Baglin, J. E. E. Tan, T. Y. Hodgson, R. T. **'Laser Annealing of Silicon Implanted with Both Argon and Arsenic'** ***Appl. Phys. Letters, 37, 81-83 (1980)*** *Comment : R, dR. 30-40 keV As Ar -> Si*	**1980-Rimi**
1980	Wada, Y. Hashimoto, N. **'Arsenic Ion-Implantated Shallow Junction'** ***J. Electrochem. Soc., 127, 461-466 (1980)*** *Comment : R, dR. 40-120 keV As -> Si*	**1980-Wada**
1981	Nakata, J. Kajiyama, K. **'Novel Low Temperature (< 300C) Annealing of Amorphous Silicon by Scanned High Energy (2.5 MeV) Heavy Ion Beam'** ***Jap. J. Appl. Phys., 21 (suppl. 21-1), 211-216 (1981)*** *Comment : R. As (50-100 keV) -> Si*	**1981-Naka**

Citations for Ion : As

Pub. Year	Authors, Title, Journal Citation and Comments	Citation Numb
1981	Nakata, J. Takahashi, M. Kajiyama, K. **'In-situ Self Ion Beam Annealing of Damage in Si during High Energy As Ion Implantation'** ***Jap. J. Appl. Phys., 20, 2211-2221 (1981)*** *Comment : R. As (0.5-2.56 MeV) -> Si*	**1981-Naka2**
1981	Takahashi, M. Nakata, J. Kajiyama, K. **'High Energy As Ion Implantation into Si - Arsenic Profiles and Electrical Activation Characteristics'** ***Jap. J. Appl. Phys., 2205-2209 (1981)*** *Comment : R. As (0.2-2.5 MeV) -> Si*	**1981-Taka**
1982	Byrne, P. F. Cheung, N. W. Sadana, D. K. **'Megavolt Arsenic Implantation into Silicon'** ***Thin Sol. Films, 363-367 (1982)*** *Comment : R. As (11 MeV) -> Si*	**1982-Byrn**
1982	Nakata, J. Kajiyama, K. **'Precise Profiles for Arsenic Implanted in Si and SiO2 over a Wide Implantation Energy Range (10 keV - 2.56 MeV)'** ***Jap. J. Appl. Phys., 21, 1363-1369 (1982)*** *Comment : R. As (10 keV - 2.56 MeV) -> Si, SiO2*	**1982-Naka**
1982	Nakata, J. Kajiyama, K. **'Novel Low Temperature Recrystallization of Amorphous Silicon by High Energy Ion Beam'** ***Appl. Phys. Letters, 40, 686-688 (1982)*** *Comment : R. Kr, As (2.5 MeV) -> Si*	**1982-Naka2**
1983	Byrne, P. F. Cheung, N. W. Sadana, D. K. Polla, D. L. **'Electrical Characteristics of Silicon Implanted with 11 MeV Arsenic'** ***Proc. Elec. Chem. Soc., 5/83, 589-594 (1983)*** *Comment : R. As (11 MeV) -> Si*	**1983-Byrn2**
1984	Byrne, P. F. Cheung, N. M. Tam, S. Hu, C. Shih, Y. C. **'Megavolt Boron and Arsenic Implantation into Silicon'** ***Mat. Res. Soc. Sym., 27,253-258 (1984)*** *Comment : R, dR. B, As (4-11 MeV) -> Si*	**1984-Byrn**
1984	Vander Vorst, W. Maes, H. E. de Keersmaecker, R. F. **'Secondary Ion Mass Spectrometry: Depth Profiling of Shallow As Implants in Silicon and SiO2'** ***J. Appl. Phys., 56, 1425-1433 (1984)*** *Comment : R. As (4-40 keV) -> Si*	**1984-Vand**

Citations for Ion : As

Pub. Year	Authors, Title, Journal Citation and Comments	Citation Numb
1985	Jeynes, C. Kimber, A. C. **'High Accuracy Data for RBS: Measurements of Range and Straggling of 60-400 keV As into Si'** ***J. Phys. D: Appl. Phys., 18, L93-97 (1985)*** *Comment : R, dR. As (60-400 keV) -> Si*	**1985-Jeyn**
1988	Grande, P. L. Fichtner, P. F. P. Behar, M. Zawislak, F. C. **'Range Profiles of Medium and Heavy Ions Implanted into SiO2'** ***Nucl. Inst. Methods, B35, 17-20 (1988)*** *Comment : R. As, Cs, Xe, Eu, Yb (10-200 keV) -> SiO2*	**1988-Gran**
1988	Tan, C. Y Xia, Y. Y. Yang, H. Sun, X. F. **'Stopping Powers of 100-600 keV F+, Ar+, As+, Br+, and Xe+ Ions in Silicon'** ***Nucl. Inst. Methods, B33, 142-146 (1988)*** *Comment : S. F, Ar, As, Br, Xe (100-600 keV) -> Si*	**1988-Tan**
1989	Xia, Y. Tan, C. Yang, H. Sun, X. Liu, J. **'Nucleonic Stopping Powers Derived from Range Measurements for Ions at Low Velocity'** ***Vacuum, 39, 347-349 (1989)*** *Comment : S, R. F, Ar, As, Br, Xe -> PbSn, Si*	**1989-Xia**
1996	Gelfort, S. Kerkow, H. Stolle, R. Petukhov, V. P. Romanowski, E. A. **'Angular Dependence of the Electronic Energy Loss for Low Energy Heavy Ions under Channeling Conditions'** ***Nucl. Inst. Methods, B115, 315-318 (1996)*** *Comment : S. Channeling of ions He to Kr in Si <110>*	**1996-Gelf**
2007	Yu, Y.C. Hsu, J.Y. Chen, K.M. **'Energy loss in polycarbonate and polyethylene terephthalate by 2.0-6.5 MeV 14N, 31P and 75As ions'** ***Nucl. Instrum. Methods B 261 (2007) 1184 (2007)*** *Comment : S. N (2-6 MeV), P (3.0-6.5 MeV), As (3.0-6.5 MeV) -> polycarbonate, polyethylene terephthalate*	**2007-Yu**